

(19)



JAPANESE PATENT OFFICE

PATENT ABSTRACTS OF JAPAN

(11) Publication number: **07130751 A**

(43) Date of publication of application: 19.05.95

(51) Int. Cl.

**H01L 21/3213**

**G03F 7/32**

**H01L 21/027**

**H01L 21/3205**

**// H01L 29/786**

(21) Application number: **05176101**

(22) Date of filing: **22.06.93**

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(54) **METHOD OF PATTERNING ALUMINUM SYSTEM  
METAL FILM**

apparatus as one process.

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(57) Abstract:

PURPOSE: To reduce the number of processes, improve the yield and improve the throughput when the aluminum system metal film of a semiconductor device is patterned into a required pattern.

CONSTITUTION: A photoresist layer 3 is applied to an aluminum film 2 formed on the upper surface of an insulating substrate 1 and the photoresist layer 3 is exposed so as to have a required pattern with a glass mask 4. While the exposed photoresist layer 3 is developed by developer (TMAH) containing 1ppm 1000ppm of chlorine ions, the foundation side aluminum film 2 is etched by the developer. As the TMAH developer functions not only as the developer of the photoresist layer 3 but also as the etchant of the aluminum film 2, the development process of the photoresist layer and the etching process using the photoresist layer can be performed in a same

